

CORRECTION

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Cite this: *Mater. Horiz.*, 2026, 13, 2595

DOI: 10.1039/d6mh90009g

rsc.li/materials-horizons

Correction: Highly-efficient and scalable TrioN (3N0C) synaptic cell for analog process-in-memory

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Correction for 'Highly-efficient and scalable TrioN (3N0C) synaptic cell for analog process-in-memory' by Junyoung Choi *et al.*, *Mater. Horiz.*, 2025, **12**, 7509–7519, <https://doi.org/10.1039/D5MH00324E>.

The authors wish to clarify that in the Acknowledgements section of the published article, the project number quoted for the “National R&D Program through the National Research Foundation of Korea (NRF) funded by Ministry of Science and ICT” should read “RS-2024-00405960” instead of “2410000283, RS-2024-00405960, 23008-45FC”.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

